

MMBD914L

Switching Diode, High Speed, 100 V

Features

- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Reverse Voltage	V_R	100	V
Forward Current	I_F	200	mA
Non-Repetitive Peak Forward Surge Current $t = 1 \text{ sec}$ $t = 1 \mu\text{sec}$	I_{FSM}	1.0 2.0	A
Peak Forward Surge Current	$I_{FM(\text{surge})}$	500	mA

THERMAL CHARACTERISTICS

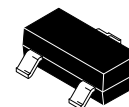
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

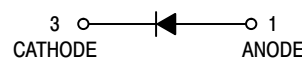


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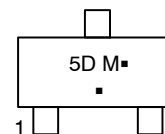
www.onsemi.com



SOT-23
CASE 318
STYLE 8



MARKING DIAGRAM



5D = Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBD914LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
SMMBD914LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBD914LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
SMMBD914LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

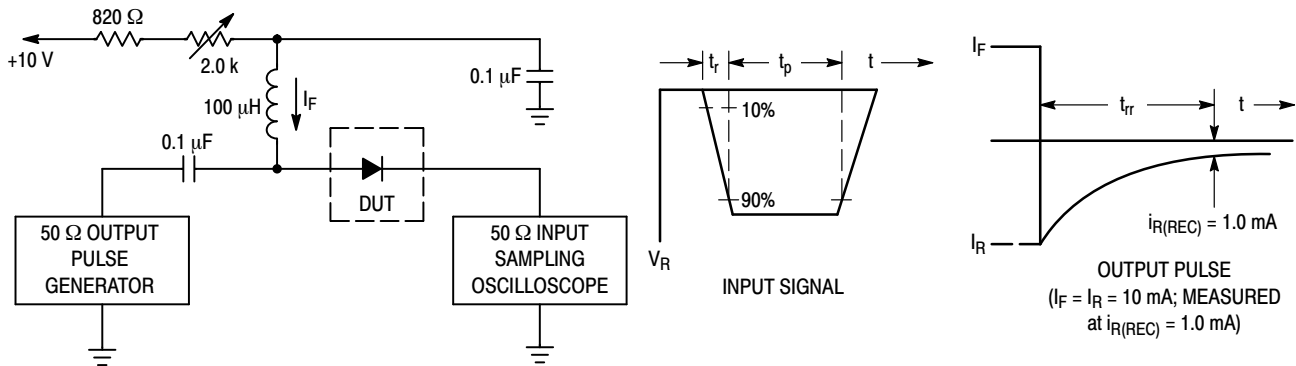
MMBD914L

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Reverse Breakdown Voltage ($I_R = 100 \mu\text{A}$)	$V_{(BR)}$	100	-	Vdc
Reverse Voltage Leakage Current ($V_R = 20 \text{ Vdc}$) ($V_R = 75 \text{ Vdc}$)	I_R	- -	25 5.0	nA dc μA dc
Diode Capacitance ($V_R = 0, f = 1.0 \text{ MHz}$)	C_T	-	4.0	pF
Forward Voltage ($I_F = 10 \text{ mA}$)	V_F	-	1.0	Vdc
Reverse Recovery Time ($I_F = I_R = 10 \text{ mA}$) (Figure 1)	t_{rr}	-	4.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

- FR-5 = $1.0 \times 0.75 \times 0.062$ in.
- Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.



- Notes:
1. A 2.0 k Ω variable resistor adjusted for a Forward Current (I_F) of 10 mA.
 2. Input pulse is adjusted so $I_{R(\text{peak})}$ is equal to 10 mA.
 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

MMBD914L

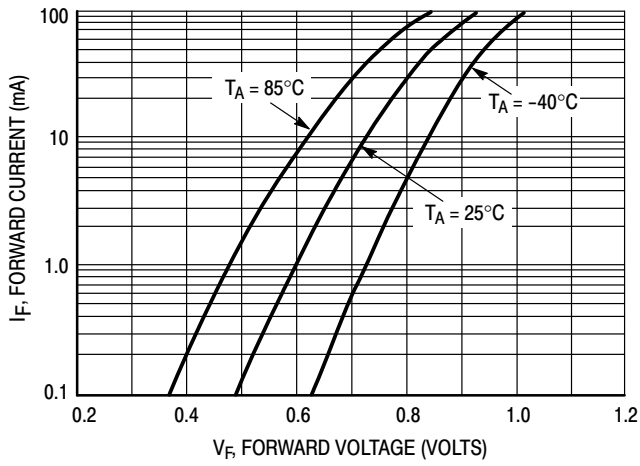


Figure 2. Forward Voltage

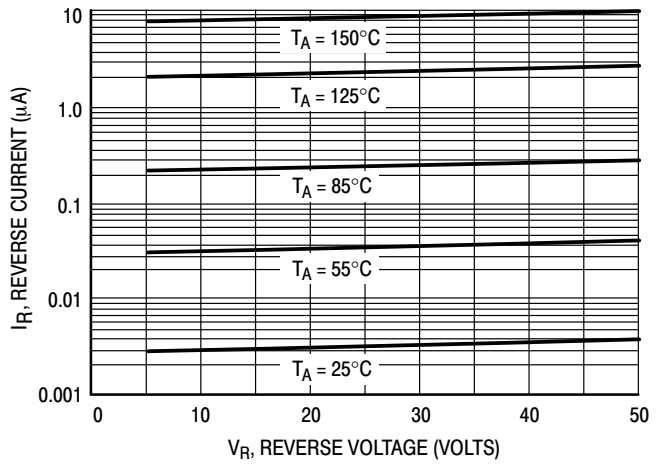


Figure 3. Leakage Current

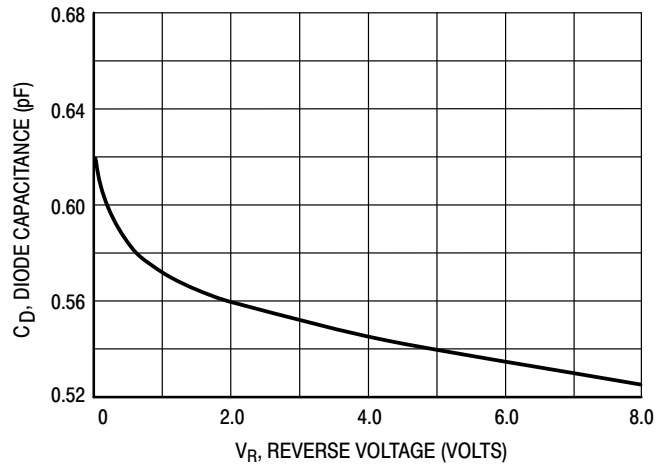


Figure 4. Capacitance

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SOT-23 (TO-236)
CASE 318-08
ISSUE AS

DATE 30 JAN 2018

SCALE 4:1



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
c	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
T	0°	---	10°	0°	---	10°

RECOMMENDED SOLDERING FOOTPRINT



GENERIC MARKING DIAGRAM*



XXX = Specific Device Code
M = Date Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present.

- | | | | |
|---|---|---|--|
| STYLE 1 THRU 5:
CANCELLED | STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 7:
PIN 1. EMITTER
2. BASE
3. COLLECTOR | STYLE 8:
PIN 1. ANODE
2. NO CONNECTION
3. CATHODE |
| STYLE 9:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 10:
PIN 1. DRAIN
2. SOURCE
3. GATE | STYLE 11:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE | STYLE 12:
PIN 1. CATHODE
2. CATHODE
3. ANODE |
| STYLE 13:
PIN 1. SOURCE
2. DRAIN
3. GATE | STYLE 14:
PIN 1. CATHODE
2. GATE
3. ANODE | STYLE 15:
PIN 1. GATE
2. CATHODE
3. ANODE | STYLE 16:
PIN 1. ANODE
2. CATHODE
3. CATHODE |
| STYLE 17:
PIN 1. NO CONNECTION
2. ANODE
3. CATHODE | STYLE 18:
PIN 1. NO CONNECTION
2. CATHODE
3. ANODE | STYLE 19:
PIN 1. CATHODE
2. ANODE
3. CATHODE-ANODE | STYLE 20:
PIN 1. CATHODE
2. ANODE
3. GATE |
| STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN | STYLE 22:
PIN 1. RETURN
2. OUTPUT
3. INPUT | STYLE 23:
PIN 1. ANODE
2. ANODE
3. CATHODE | STYLE 24:
PIN 1. GATE
2. DRAIN
3. SOURCE |
| STYLE 25:
PIN 1. ANODE
2. CATHODE
3. GATE | STYLE 26:
PIN 1. CATHODE
2. ANODE
3. NO CONNECTION | STYLE 27:
PIN 1. CATHODE
2. CATHODE
3. CATHODE | STYLE 28:
PIN 1. ANODE
2. ANODE
3. ANODE |

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